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**William M. Tong
Douglas J. Resnick**
Editors

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Joy Y. Cheng, IBM Almaden Research Center (United States)

DSA Metrology and Inspection: Joint Session with Conferences 8680 and 8681
Joy Y. Cheng, IBM Almaden Research Center (United States)
Martha I. Sanchez, IBM Almaden Research Center (United States)

E-Beam Direct-Write for High-Volume Manufacturing II
Shy-Jay Lin, Taiwan Semiconductor Manufacturing Company Ltd. (Taiwan)
Hans Loeschner, IMS Nanofabrication AG (Austria)

Nanoimprint Applications
Elizabeth A. Dobisz, HGST (United States)
John G. Maltabes, Hewlett-Packard Laboratories (United States)

Design for Manufacturability for DSA: Joint Session with Conferences
8680 and 8684

Benjamin M. Rathsack, Tokyo Electron America, Inc. (United States)

Lars W. Liebmann, IBM Corporation (United States)

DSA Vias

James Watkins, University of Massachusetts Amherst (United States)

Benjamin M. Rathsack, Tokyo Electron America, Inc. (United States)

Nanoprobe Array Direct-Write Technologies

Ivo W. Rangelow, Technische Universität Ilmenau (Germany)

Frank M. Schellenberg, Consultant (United States)

E-Beam Direct-Write for High-Volume Manufacturing III

Ines A. Stolberg, Vistec Electron Beam Lithography Group (Germany)

Marco Wieland, MAPPER Lithography (Netherlands)

DSA Lines-Spaces

Frank M. Schellenberg, Consultant (United States)

Christopher Bencher, Applied Materials, Inc. (United States)